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	Application No.	Applicant(s)
Notice of Allowability	10/821,425	PAUL D. HURWITZ
	Examiner	Art Unit
	Thanh Y. Tran	2822
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap) or other appropriate communicatio IGHTS. This application is subject	oplication. If not included n will be mailed in due course. THIS
1. This communication is responsive to		
2. The allowed claim(s) is/are <u>1-20</u> .		
3. \boxtimes The drawings filed on <u>09 April 2004</u> are accepted by the E	xaminer.	
4. ☐ Acknowledgment is made of a claim for foreign priority una) ☐ All b) ☐ Some* c) ☐ None of the: 1. ☐ Certified copies of the priority documents have 2. ☐ Certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received:	e been received. e been received in Application No	
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file a reply MENT of this application.	complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv		
6. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date(b) including changes required by the attached Examiner Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the state of	son's Patent Drawing Review(PTC - 's Amendment / Comment or in the 1.84(c)) should be written on the draw	Office action of ings in the front (not the back) of
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT		
Attachment(s) 1. ☑ Notice of References Cited (PTO-892)	5. Notice of Informal	Patent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Summar	
3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date <u>5/10/04</u>	Paper No./Mail Da 08), 7. Examiner's Amend	are Iment/Comment
4. ☐ Examiner's Comment Regarding Requirement for Deposit	8. 🛛 Examiner's Statem	nent of Reasons for Allowance
of Biological Material	9. 🔲 Other	
	AMI	R ZARABIAN

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DETAILED ACTION

Allowable Subject Matter

1. Claims 1-20 are allowed.

2. The following is an examiner's statement of reasons for allowance:

The prior art of record does not teach or render obvious, at least to the skilled artisan, the instant invention regarding a method for forming an NPN device and a vertical PNP device on a substrate by the steps: forming an opening in the buffer layer which is formed on the insulating layer, forming a semiconductor layer on the buffer layer and in the opening, the semiconductor layer has a first portion which is situated in the opening in the NPN region, and a second portion of the semiconductor layer is situated on the buffer layer in the PNP region; wherein the first portion forms a single crystal base of the NPN device, and the second portion forms a polycrystalline emitter of said vertical PNP device, in combination with other claim limitations, as recited in independent claim 1.

The prior art of record does not teach or render obvious, at least to the skilled artisan, the instant invention regarding a structure comprising: a buffer layer has an opening and is situated on the insulating layer, a semiconductor layer is situated on the buffer layer and in the opening, the semiconductor layer has a first portion which is situated in the opening, and a second portion of the semiconductor layer is situated on the buffer layer in the PNP region; wherein the first portion forms a single crystal base of the NPN device, and the second portion forms a polycrystalline emitter of said vertical PNP device, in combination with other claim limitations, as recited in independent claim 8.

The prior art of record does not teach or render obvious, at least to the skilled artisan, the instant invention regarding a method for forming an NPN device and a vertical PNP device on a substrate by the steps: forming a first opening in the insulating layer in the PNP region; forming a second opening in the buffer layer; forming a semiconductor layer on the buffer layer and in the second opening, the semiconductor layer has a first portion which is situated in the second opening in the NPN region, and a second portion of the semiconductor layer is situated on the buffer layer in the PNP region; wherein the first portion forms a single crystal base of the NPN device, and the second portion forms a polycrystalline emitter of said vertical PNP device, in combination with other claim limitations, as recited in independent claim 15.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanh Y. Tran whose telephone number is (571) 272-2110. The examiner can normally be reached on M-F (9-6:30pm).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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ÁMIR ZARABIÁN FRVISORY PATENT EXAMINER

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